

## P-Channel Enhancement Mode Power MOSFET

### Description

The RM18P100HDE uses advanced trench technology and design to provide excellent  $R_{DS(ON)}$  with low gate charge. It can be used in a wide variety of applications. It is ESD protected.

### General Features

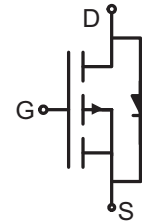
- $V_{DS} = -100V, I_D = -18A$   
 $R_{DS(ON)} < 100m\Omega @ V_{GS} = -10V$  (Typ:85m $\Omega$ )
- Super high dense cell design
- Advanced trench process technology
- Reliable and rugged
- High density cell design for ultra low On-Resistance

### Application

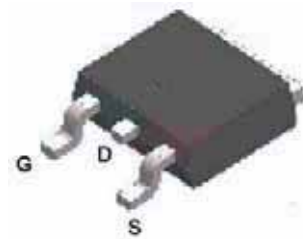
- Power management in notebook computer
- Portable equipment and battery powered systems
- Halogen-free
- P/N suffix V means AEC-Q101 qualified, e.g:RM18P100HDEV

**100% UIS TESTED!**

**100%  $\Delta V_{ds}$  TESTED!**



Schematic diagram



TO-263-2L top view  
pin assignment

### Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
18P100	RM18P100HDE	TO-263-2L	-	-	-

### Absolute Maximum Ratings ( $T_C = 25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	$V_{DS}$	-100	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Drain Current-Continuous	$I_D$	-18	A
Drain Current-Continuous( $T_C = 100^\circ C$ )	$I_D(100^\circ C)$	-12	A
Pulsed Drain Current	$I_{DM}$	-72	A
Maximum Power Dissipation	$P_D$	70	W
Derating factor		0.56	W/ $^\circ C$
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 To 150	$^\circ C$

## Thermal Characteristic

Thermal Resistance, Junction-to-Case (Note 2)	$R_{\theta Jc}$	1.79	$^{\circ}\text{C/W}$
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## Electrical Characteristics ( $T_c=25^{\circ}\text{C}$ unless otherwise noted)

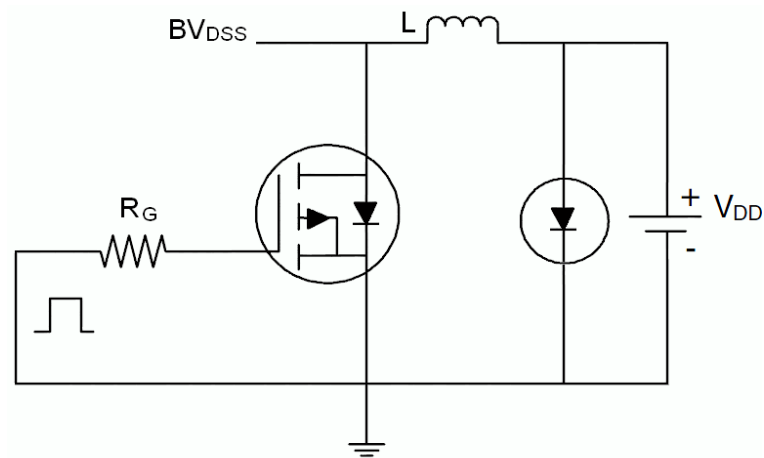
Parameter	Symbol	Condition	Min	Typ	Max	Unit
<b>Off Characteristics</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS}=0V, I_D=-250\mu A$	-100	-	-	V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=-100V, V_{GS}=0V$	-	-	1	$\mu A$
Gate-Body Leakage Current	$I_{GSS}$	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	$\pm 20$	$\mu A$
<b>On Characteristics (Note 3)</b>						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=-250\mu A$	-1	-1.9	-3	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS}=-10V, I_D=-16A$	-	85	100	m $\Omega$
Forward Transconductance	$g_{FS}$	$V_{DS}=-50V, I_D=-10A$	5	-	-	S
<b>Dynamic Characteristics (Note4)</b>						
Input Capacitance	$C_{iss}$	$V_{DS}=-25V, V_{GS}=0V,$ $F=1.0\text{MHz}$	-	1300	-	PF
Output Capacitance	$C_{oss}$		-	400	-	PF
Reverse Transfer Capacitance	$C_{rss}$		-	240	-	PF
<b>Switching Characteristics (Note 4)</b>						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=-50V, I_D=-16A$ $V_{GS}=-10V, R_{GEN}=9.1\Omega$	-	16	-	nS
Turn-on Rise Time	$t_r$		-	73	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	34	-	nS
Turn-Off Fall Time	$t_f$		-	57	-	nS
Total Gate Charge	$Q_g$	$V_{DS}=-80V, I_D=-16A,$ $V_{GS}=-10V$	-	61	-	nC
Gate-Source Charge	$Q_{gs}$		-	14	-	nC
Gate-Drain Charge	$Q_{gd}$		-	29	-	nC
<b>Drain-Source Diode Characteristics</b>						
Diode Forward Voltage (Note 3)	$V_{SD}$	$V_{GS}=0V, I_S=-10A$	-	-	-1.2	V
Diode Forward Current (Note 2)	$I_S$	-	-	-	-18	A
Reverse Recovery Time	$t_{rr}$	$T_J = 25^{\circ}\text{C}, I_F = -16A$ $di/dt = 100A/\mu s(\text{Note3})$	-	88.3	-	nS
Reverse Recovery Charge	$Q_{rr}$		-	65.9	-	nC
Forward Turn-On Time	$t_{on}$	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)				

### Notes:

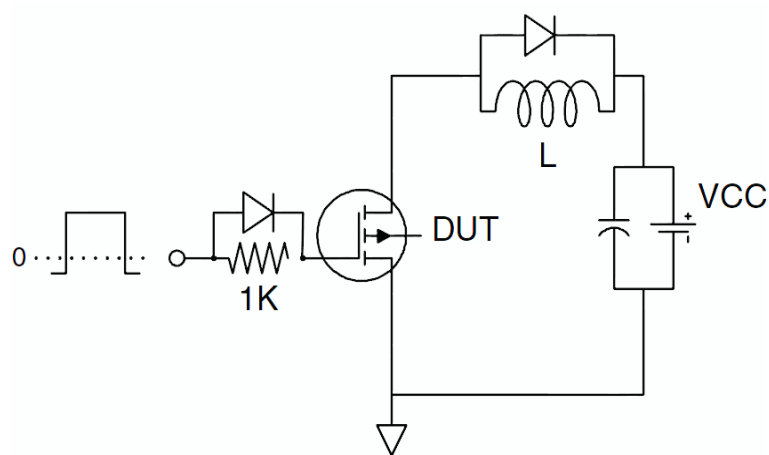
1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board,  $t \leq 10$  sec.
3. Pulse Test: Pulse Width  $\leq 300\mu s$ , Duty Cycle  $\leq 2\%$ .
4. Guaranteed by design, not subject to production
5. EAS condition:  $T_J=25^{\circ}\text{C}, V_{DD}=-50V, V_G=-10V, L=0.5\text{mH}, R_g=25\Omega$

## Test Circuit

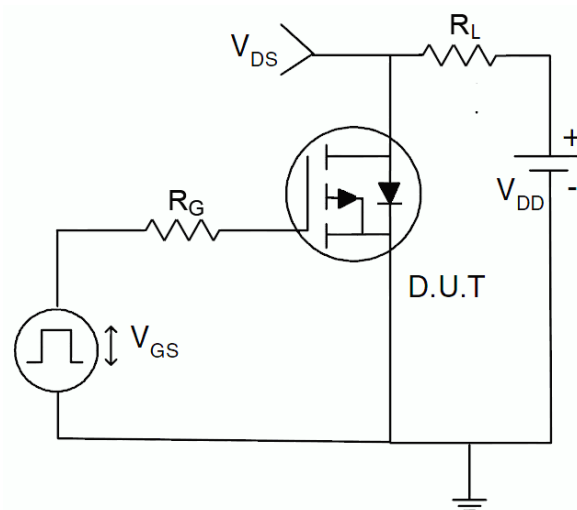
### 1) $E_{AS}$ Test Circuit



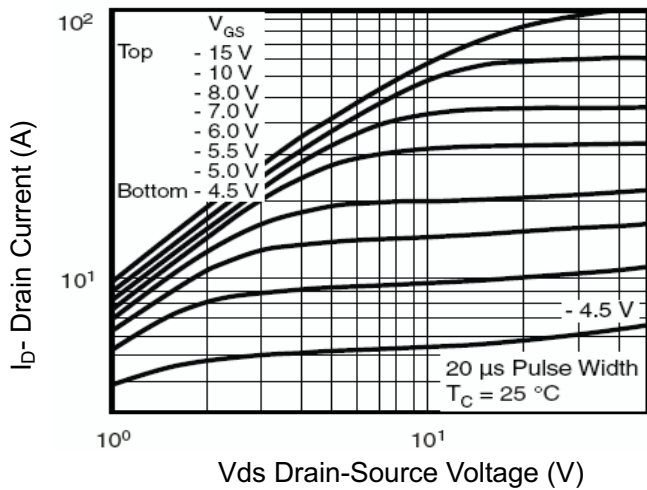
### 2) Gate Charge Test Circuit



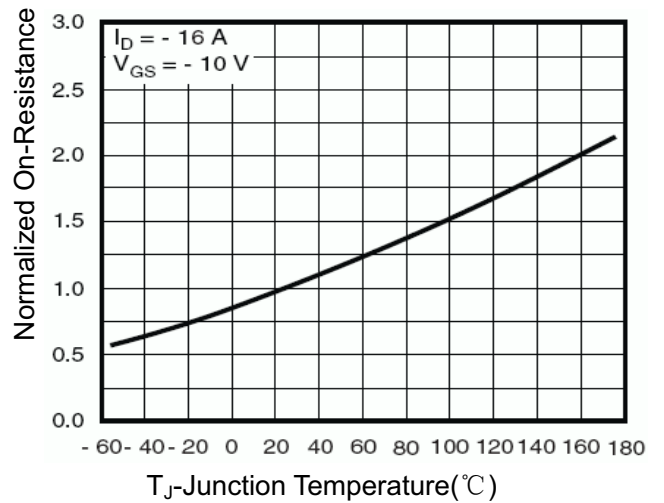
### 3) Switch Time Test Circuit



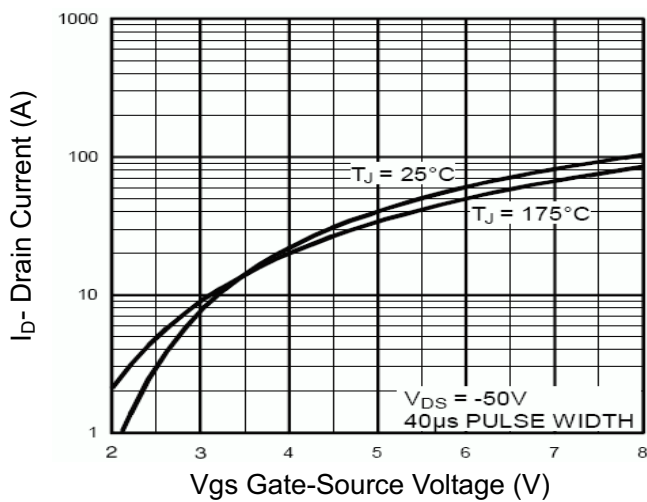
## RATING AND CHARACTERISTICS CURVES (RM18P100HDE)



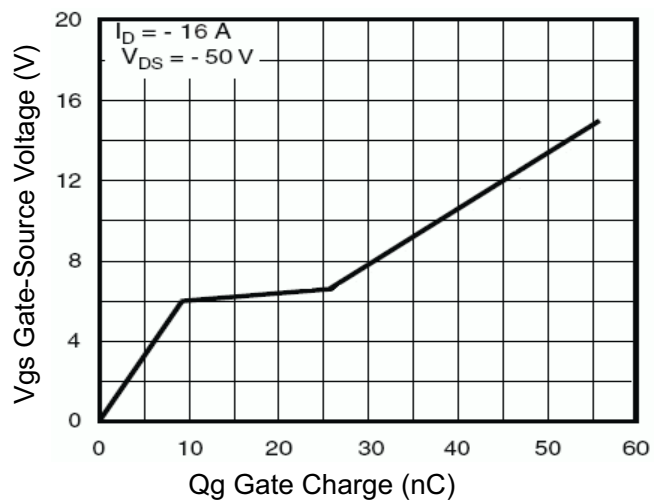
**Figure 1 Output Characteristics**



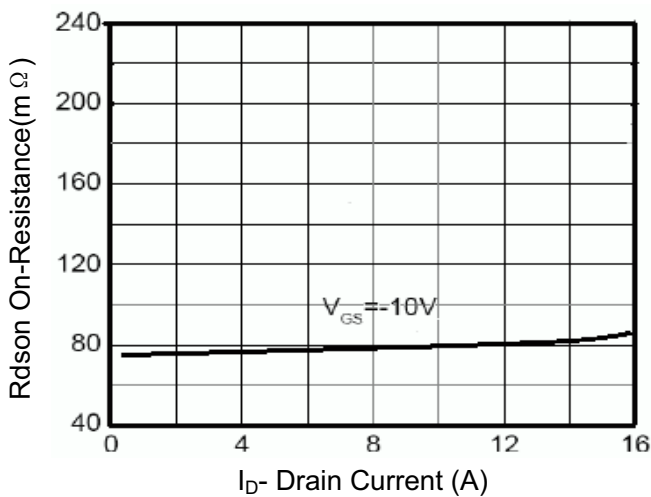
**Figure 4 Rdson-Junction Temperature**



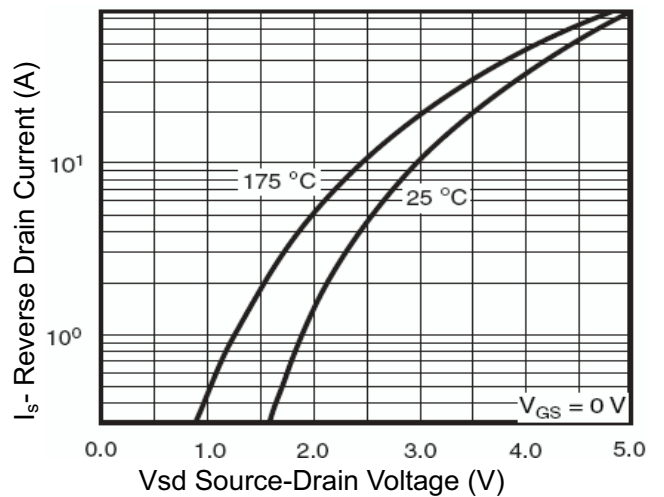
**Figure 2 Transfer Characteristics**



**Figure 5 Gate Charge**

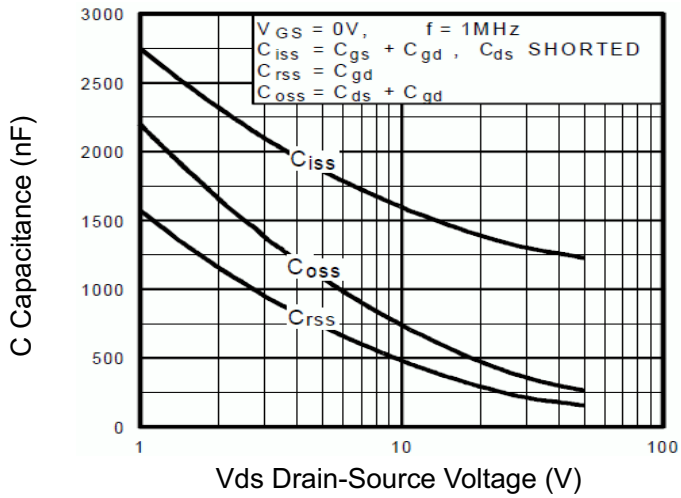


**Figure 3 Rdson- Drain Current**

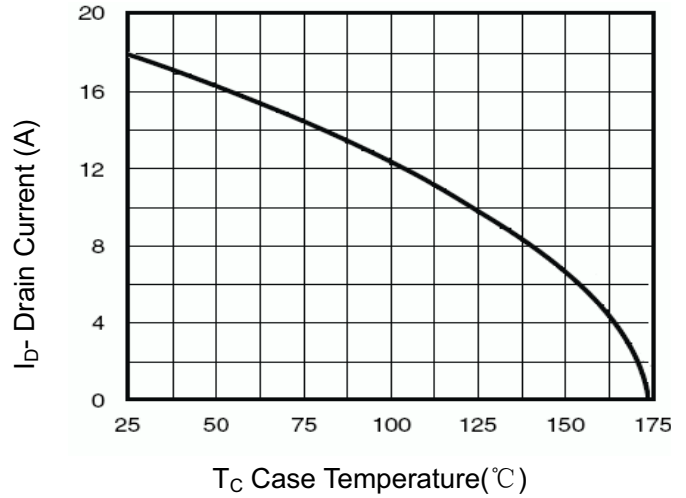


**Figure 6 Source- Drain Diode Forward**

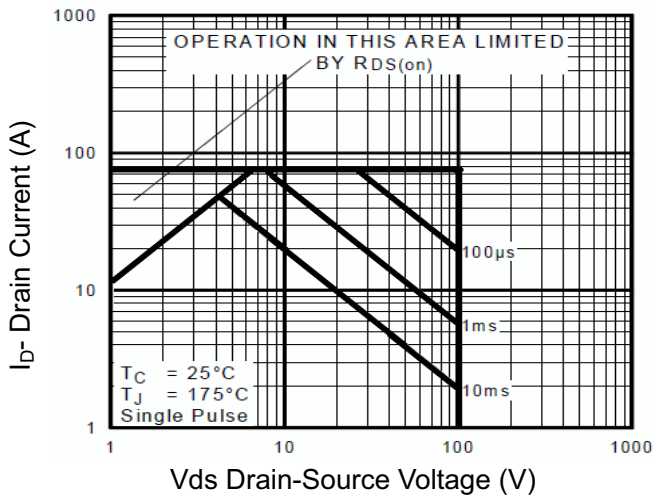
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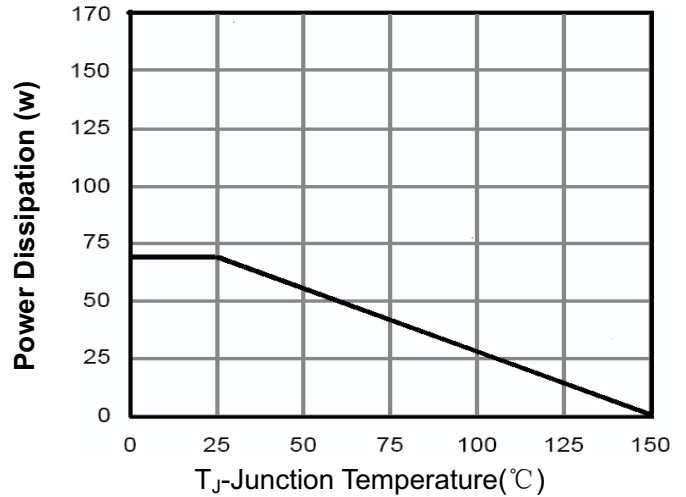
**Figure 7 Capacitance vs Vds**



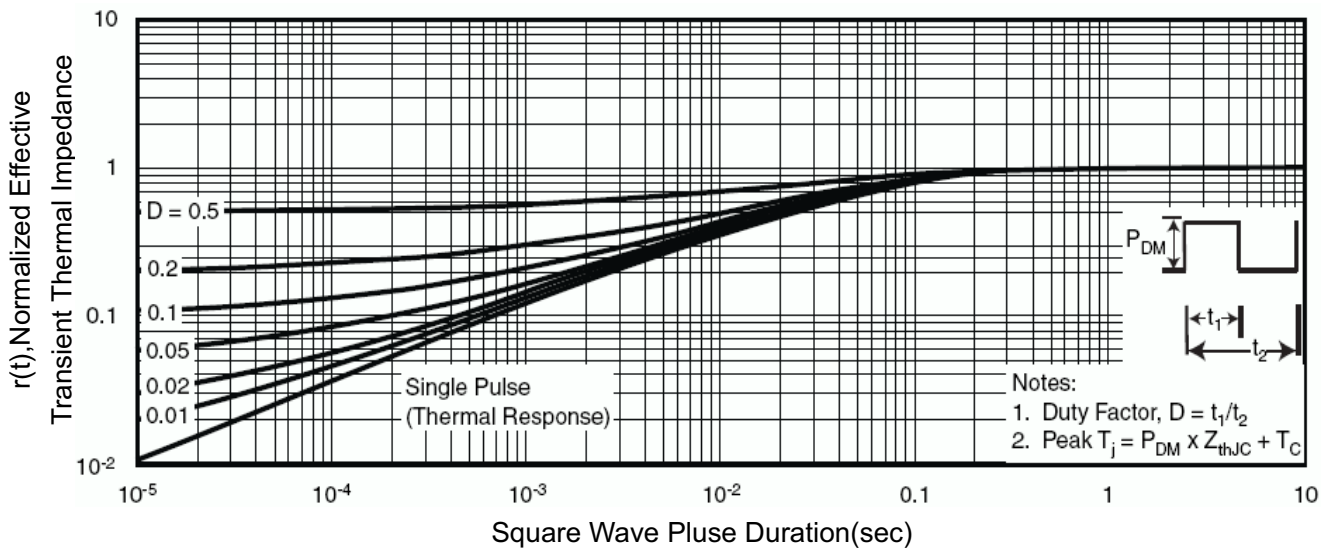
**Figure 9 Drain Current vs Case Temperature**



**Figure 8 Safe Operation Area**

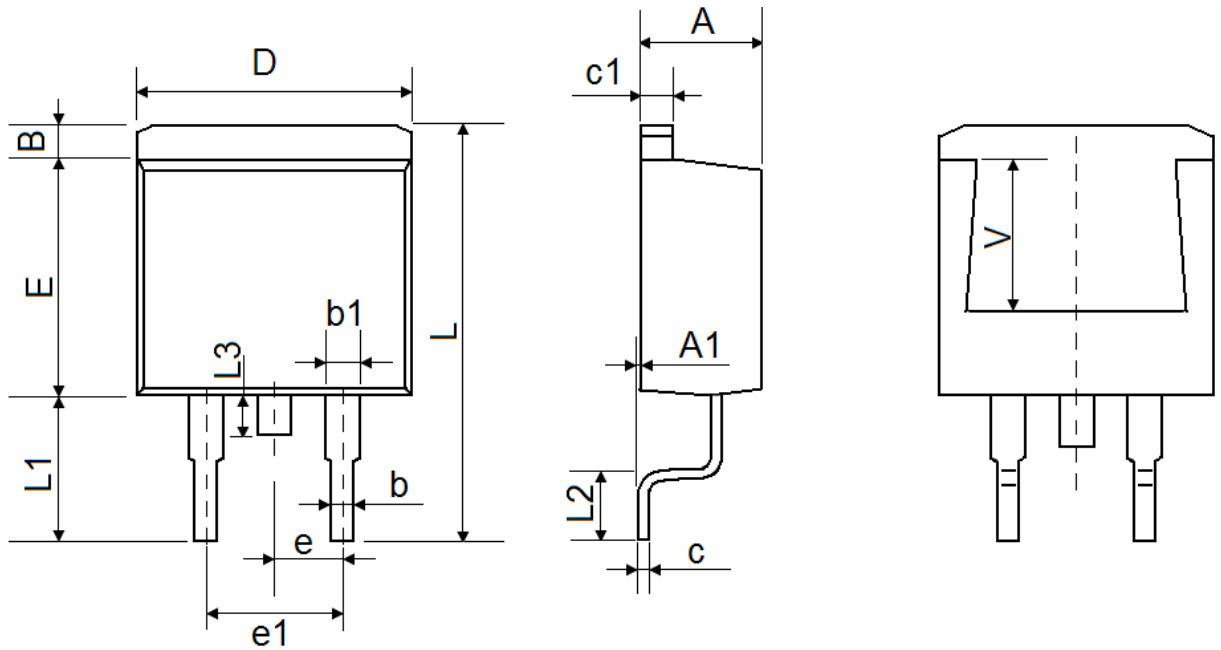


**Figure 10 Power De-rating**



**Figure 11 Normalized Maximum Transient Thermal Impedance**

# TO-263-2L Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.470	4.670	0.176	0.184
A1	0.000	0.150	0.000	0.006
B	1.170	1.370	0.046	0.054
b	0.710	0.910	0.028	0.036
b1	1.170	1.370	0.046	0.054
c	0.310	0.530	0.012	0.021
c1	1.170	1.370	0.046	0.054
D	10.010	10.310	0.394	0.406
E	8.500	8.900	0.335	0.350
e	2.540 TYP.		0.100 TYP.	
e1	4.980	5.180	0.196	0.204
L	15.050	15.450	0.593	0.608
L1	5.080	5.480	0.200	0.216
L2	2.340	2.740	0.092	0.108
L3	1.300	1.700	0.051	0.067
V	5.600 REF		0.220 REF	

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